

AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph beginning on Page 7, line 4 with the following amended paragraph:

The apparatus 10 has a vacuum container (not shown) for containing the graphite vessel 1. The atmosphere and the pressure inside the graphite vessel 1 ~~is~~ are controlled by connecting the vacuum container to a vacuum evacuation system and a gas supplying system. The graphite vessel 1 is heated by a heating device (not shown) arranged on a periphery thereof. The temperature inside the graphite vessel 1 is controlled by adjusting the power input in the heating device.

Please replace the paragraph beginning on Page 10, line 6 with the following amended paragraph:

The resulting SiC single crystal 4a was sliced to form a cross section, and the plane distance was obtained from an electron beam diffraction image by a TEM (transmission electron microscope). As a result, the plane distance in the <0001> direction was 2.52 Å, which was equivalent to the literature value (PROPERTIES OF SILICON CARBIDE, edited by ~~Gery~~ Gary L. Harris, ~~eims~~ Eims DATA_REVIEW Series No. 13, pp. 4). The rate of change in volume per 1 mol of the crystal caused by the substitution of the impurity (i.e., arsenic) on the Si site or the C site of SiC was measured as the distortion in the crystal. The distortion in the crystal was 0.5% or less. Thus a crystal having high quality without distortion was obtained. The SiC single crystal 4a was of an n-type and had an arsenic concentration of $2.5 \times 10^{18} \text{ cm}^{-3}$ and resistivity of 120 mΩ·cm.